DATA SHEET



MOS FIELD EFFECT TRANSISTOR 2SK3365

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3365 is N-Channel MOS Field Effect Transistor designed for DC/DC converters application of notebook computers.

FEATURES

- Low on-resistance
- $\begin{array}{l} {\sf R}_{\sf DS(on)1} = 14 \mbox{ m}\Omega \mbox{ (MAX.)} \mbox{ (Vgs} = 10 \mbox{ V}, \mbox{ Id} = 15 \mbox{ A}) \\ {\sf R}_{\sf DS(on)2} = 21 \mbox{ m}\Omega \mbox{ (MAX.)} \mbox{ (Vgs} = 4.5 \mbox{ V}, \mbox{ Id} = 15 \mbox{ A}) \\ {\sf R}_{\sf DS(on)3} = 29 \mbox{ m}\Omega \mbox{ (MAX.)} \mbox{ (Vgs} = 4.0 \mbox{ V}, \mbox{ Id} = 15 \mbox{ A}) \\ \end{array}$
- Low Ciss : Ciss = 1300 pF (TYP.)
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Drain to Source Voltage ($V_{GS} = 0 V$)	Vdss	30	V
Gate to Source Voltage ($V_{DS} = 0 V$)	Vgss	±20	V
Drain Current (DC)	D(DC)	±30	А
Drain Current (Pulse) ^{Note}	D(pulse)	±120	А
Total Power Dissipation (Tc = 25 °C)	P⊤	36	W
Total Power Dissipation (T _A = 25 °C)	P⊤	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to + 150	°C

Note PW \leq 10 μ s, Duty cycle \leq 1 %

THERMAL RESISTANCE

Channel to case	Rth(ch-C)	3.48	°C/W
Channel to ambient	Rth(ch-A)	125	°C/W

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ORDERING INFORMATION

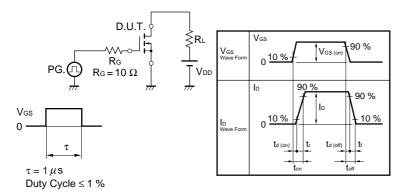
PART NUMBER	PACKAGE	
2SK3365	TO-251	
2SK3365-Z	TO-252	

查迴了我的名称 CHARGERISTICS (TA = 25 °C)

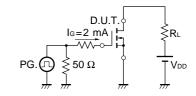
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, Id = 15 A		11.5	14	mΩ
	RDS(on)2	Vgs = 4.5 V, Id = 15 A		15.2	21	mΩ
	RDS(on)3	Vgs = 4.0 V, Id = 15 A		18	29	mΩ
Gate to Source Cut-off Voltage	V _{GS(off)}	$V_{DS} = 10 V, I_{D} = 1 mA$	1.5	2.0	2.5	V
Forward Transfer Admittance	y _{fs}	Vds = 10 V, Id = 15 A	8.0	16.0		S
Drain Leakage Current	IDSS	Vds = 30 V, Vgs = 0 V			10	μA
Gate to Source Leakage Current	lgss	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±10	μA
Input Capacitance	Ciss	Vps = 10 V, Vgs = 0 V, f = 1 MHz		1300		pF
Output Capacitance	Coss			405		pF
Reverse Transfer Capacitance	Crss			190		pF
Turn-on Delay Time	td(on)	$I_{D} = 15 \text{ A}, \text{ V}_{GS(on)} = 10 \text{ V}, \text{ V}_{DD} = 15 \text{ V},$		37		ns
Rise Time	tr	R _G = 10 Ω		500		ns
Turn-off Delay Time	td(off)			75		ns
Fall Time	tr			95		ns
Total Gate Charge	QG	ID = 30 A, VDD = 24 V, VGS = 10 V		25		nC
Gate to Source Charge	QGS			4.5		nC
Gate to Drain Charge	Qgd			7.0		nC
Body Diode forward Voltage	VF(S-D)	IF = 30 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 30 A, VGS = 0 V		35		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		32		nC

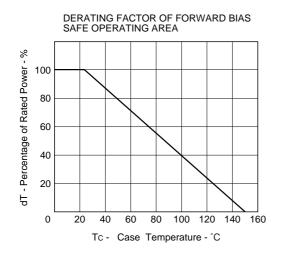
TEST CIRCUIT 1 SWITCHING TIME



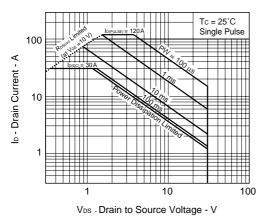
TEST CIRCUIT 2 GATE CHARGE



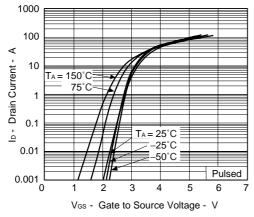
<u>李洵尼ALCARARACHER</u>TICS (TA = 25 °C)

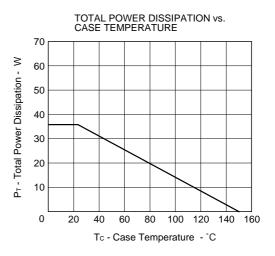


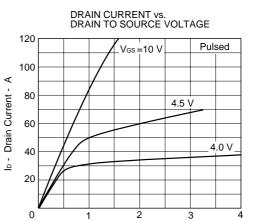
FORWARD BIAS SAFE OPERATING AREA











VDS - Drain to Source Voltage - V

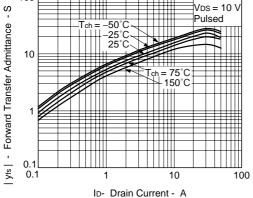
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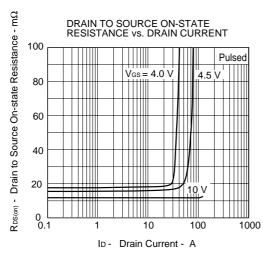
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1 000 r_{th(t)} - Transient Thermal Resistance - °C/W $R_{th(ch-A)} = 125 °C/W$ <u>T Ì H IIÍ</u> 100 10 Rth(ch-C) = 3.48 °C/Wtttt 11 1 Single Pulse 0.1 10 m 100 m 10 100 1000 100*µ* 1 m 1 PW - Pulse Width - s

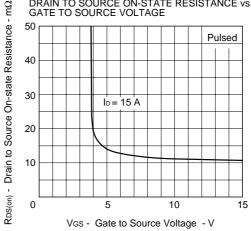
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



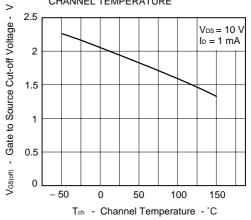




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



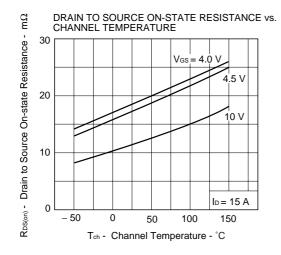
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

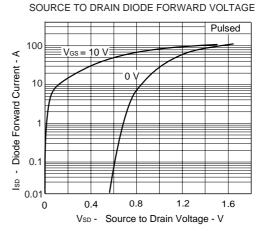


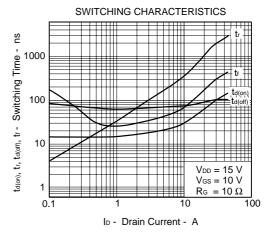
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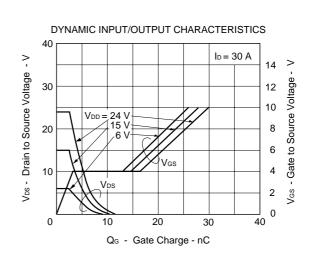
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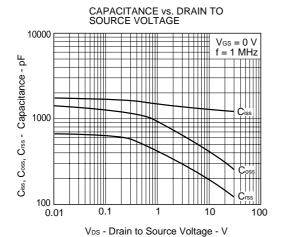
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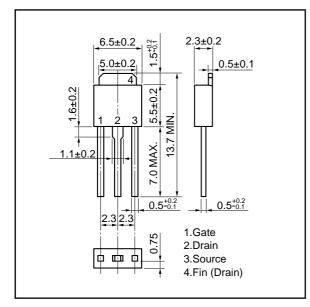




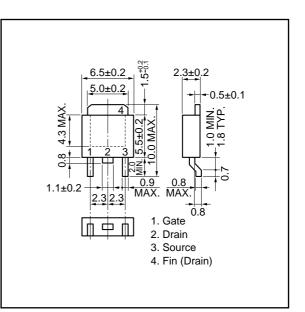
REVERSE RECOVERY TIME vs. DRAIN CURRENT 1000 di/dt = 100 A/µs Vgs = 0 V ns trr - Reverse Recovery Time -100 10 1 0.1 10 100 1 IF - Diode Current - A

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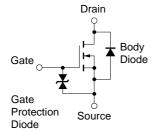
1) TO-251 (MP-3)



2) TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device. **瑜阁//2**6K3365-Z"供应商

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